

N-Channel Enhancement Mode MOSFET

1. Product Information

1.1 Features

- ☒ Advanced trench cell design
- ☒ Low Thermal Resistance

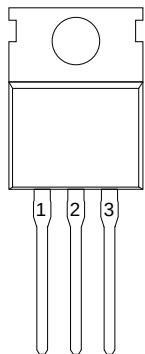
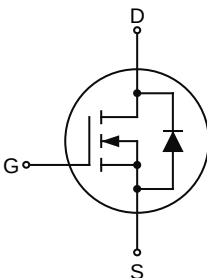
1.2 Applications

- ☒ Motor drivers
- ☒ DC/DC Converter

1.3 Quick reference

- ☒ $BV \geq 60\text{ V}$
- ☒ $R_{DS(ON)} \leq 1.5\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☒ $P_{tot} \leq 312\text{ W}$
- ☒ $R_{DS(ON)} \leq 2.0\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- ☒ $I_D \leq 200\text{ A}$

2. Pin Description

Pin	Description	Simplified Outline	Symbol
1	Gate(G)	 Top View TO-220	
2	Drain(D)		
3	Source(S)		

3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	Drain-Source Voltage	$T_C=25^{\circ}\text{C}$	-	60	V
V_{GS}	Gate-Source Voltage	$T_C=25^{\circ}\text{C}$	-	± 20	V
I_D^*	Drain Current (DC)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	200	A
		$T_C=100^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	110	A
$I_{DM}^{*,**}$	Drain Current (Pulsed)	$T_C=25^{\circ}\text{C}, V_{GS}=10\text{ V}$	-	800	A
P_{tot}^*	Drain power dissipation	$T_C=25^{\circ}\text{C}$	-	312	W
T_{stg}	Storage Temperature		-55	150	$^{\circ}\text{C}$
T_J	Junction Temperature		-	150	$^{\circ}\text{C}$
I_S	Continuous-Source Current	$T_C=25^{\circ}\text{C}$	-	200	A
E_{AS}^*	Single Pulsed Avalanche Energy	$V_{DD}=50\text{ V}, L=1.0\text{ mH}$	-	1104	mJ
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient		-	45	$^{\circ}\text{C/W}$
$R_{\theta JC}^*$	Thermal Resistance-Junction to Case		-	0.4	

Notes:

- * Surface Mounted on 1 in² pad area, $t \leq 10\text{ sec}$
- ** Pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
- *** Limited by bonding wire

4. Marking Information

Product Name	Marking
KJ011N06C	011N06 YWWXXX YWWXXX: Date Code

5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ011N06C	TO-220	-	-	50	

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

6. Electrical Characteristics (T_A=25°C Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _{DS} =250 μA	60	-	-	V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 μA	1.0	-	2.0	V
I _{DSS}	Drain Leakage Current	V _{DS} =48 V, V _{GS} =0 V	-	-	1	μA
I _{GSS}	Gate Leakage Current	V _{GS} =±20 V, V _{GS} =0 V	-	-	±100	nA
R _{DS(ON)} ^a	Drain-Source On-State Resistance	V _{GS} =10 V, I _{DS} =30 A	-	1.2	1.5	mΩ
		V _{GS} =4.5 V, I _{DS} =20 A	-	1.7	2.0	mΩ
Diode Characteristics						
V _{SD} ^a	Diode Forward Voltage	I _{SD} =30 A, V _{GS} =0 V	-	-	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =30 A, dI _{SD} /dt=100 A/μs	-	87	-	ns
Q _{rr}	Reverse Recovery Charge		-	129	-	nC
Dynamic Characteristics ^b						
C _{iss}	Input Capacitance	V _{GS} =0 V, V _{DS} =30 V Frequency=1 MHz	-	7337	-	pF
C _{oss}	Output Capacitance		-	2233	-	
C _{rss}	Reverse Transfer Capacitance		-	187	-	
t _{d(on)}	Turn-on Delay Time	V _{DS} =30 V, V _{GEN} =10 V, R _G =3.9 Ω, R _L =1 Ω, I _{DS} =30 A	-	16	-	ns
t _r	Turn-on Rise Time		-	66	-	
t _{d(off)}	Turn-off Delay Time		-	143	-	
t _f	Turn-off Fall Time		-	130	-	
Gate Charge Characteristics ^b						
Q _g	Total Gate Charge	V _{DS} =30 V, V _{GS} =10 V, I _{DS} =30 A	-	152	-	nC
Q _{gs}	Gate-Source Charge		-	27	-	
Q _{gd}	Gate-Drain Charge		-	33	-	

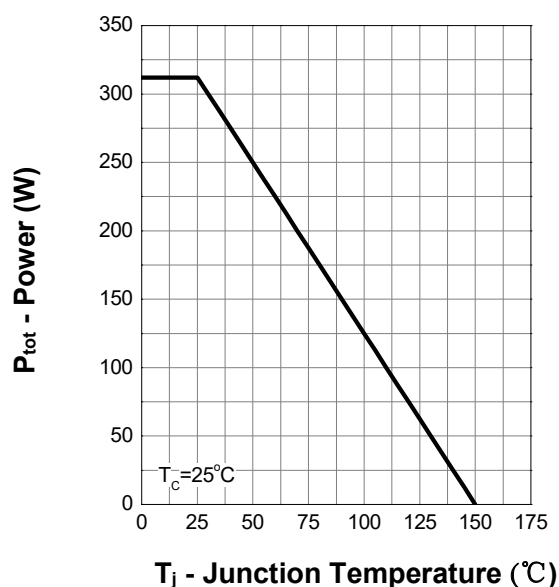
Notes:

a: Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%

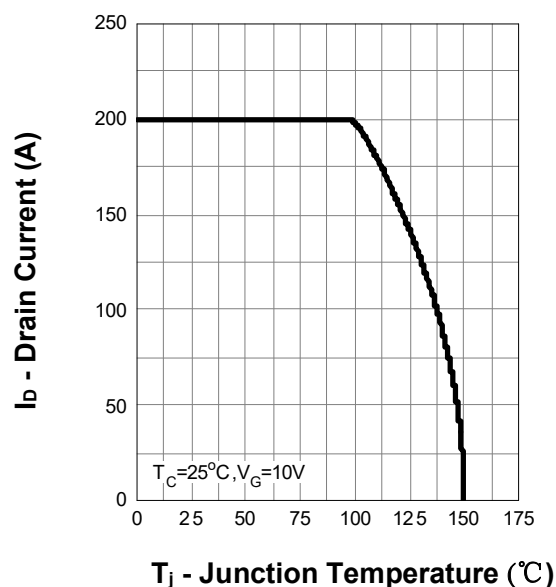
b: Guaranteed by design, not subject to production testing

7. Typical Characteristics

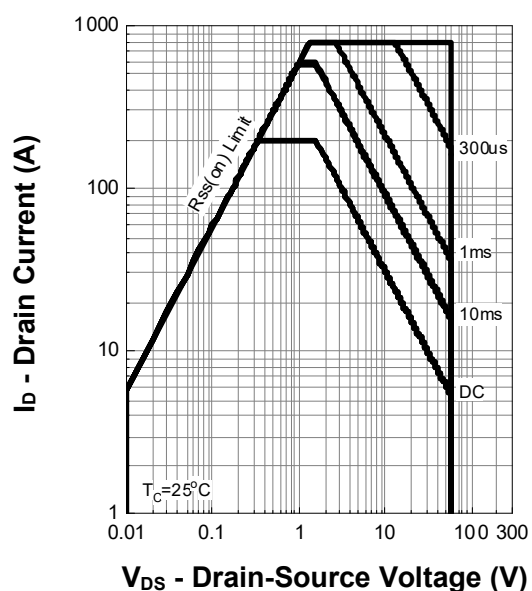
Power Capability



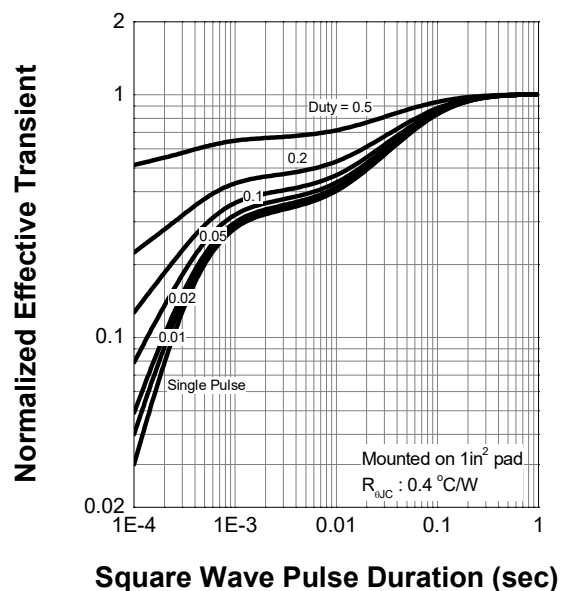
Current Capability



Safe Operation Area

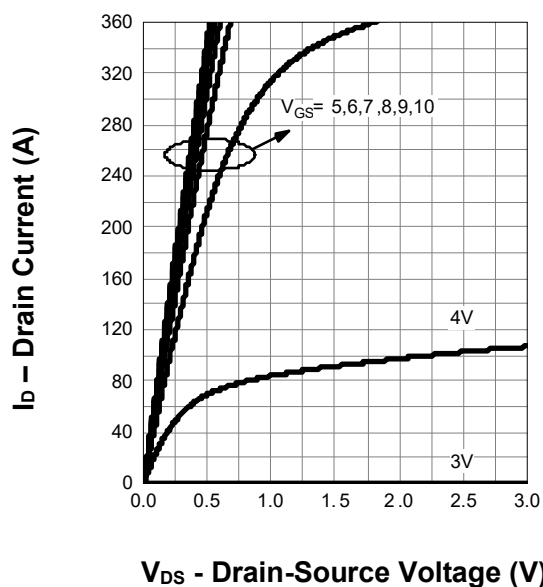


Thermal Transient Impedance

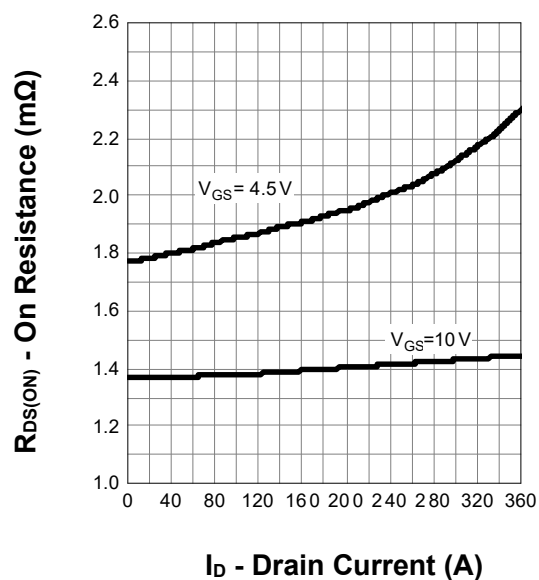


7. Typical Characteristics (Cont.)

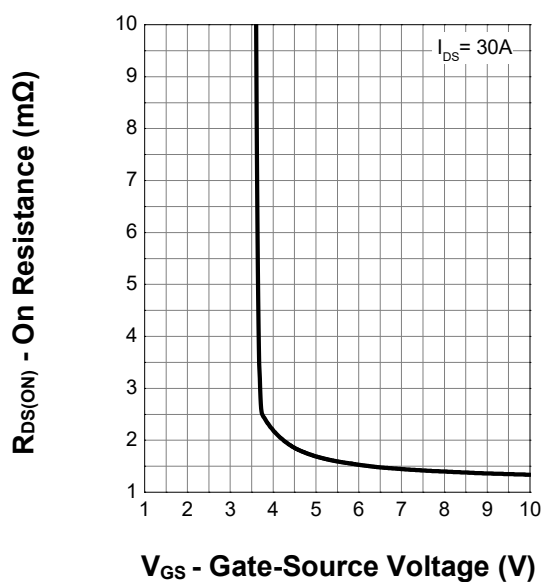
Output Characteristics



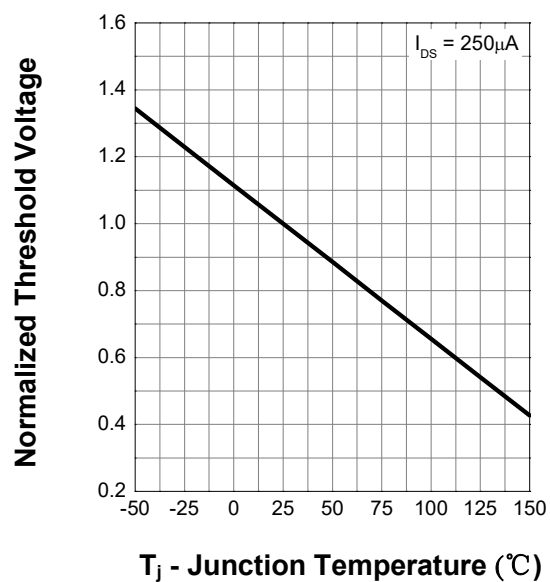
Drain-Source On Resistance



Transfer Characteristics

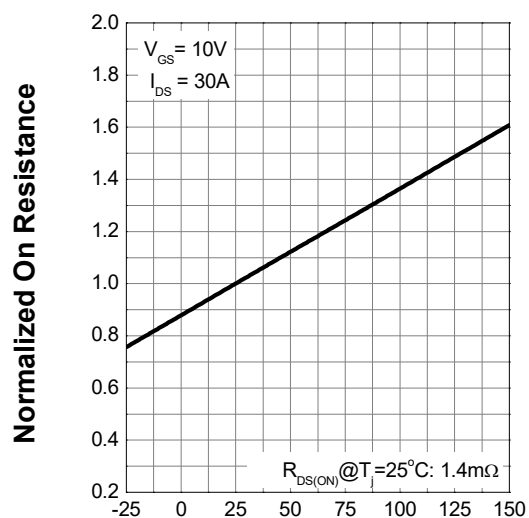


Gate Threshold Voltage



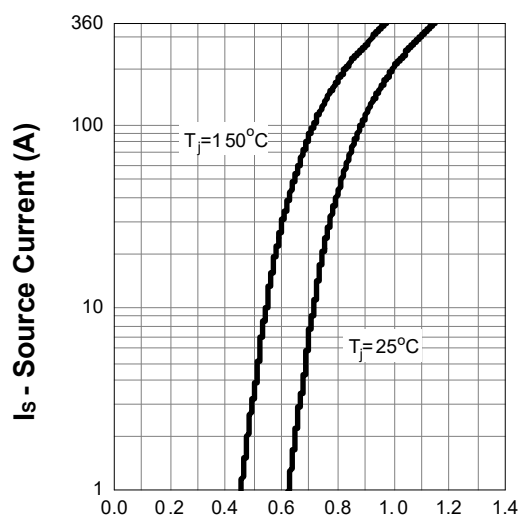
7. Typical Characteristics (Cont.)

Drain-Source On Resistance



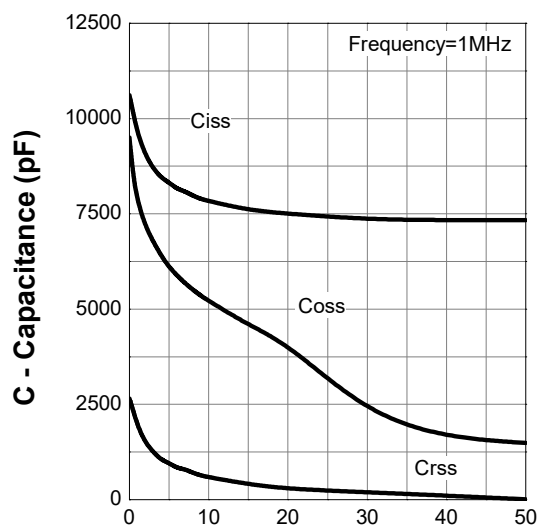
T_J - Junction Temperature ($^{\circ}\text{C}$)

Body Diode Characteristics



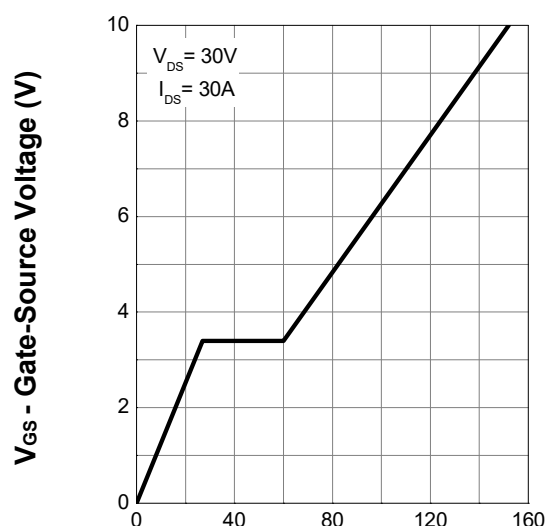
V_{SD} - Source-Drain Voltage (V)

Capacitance



V_{DS} - Drain-Source Voltage (V)

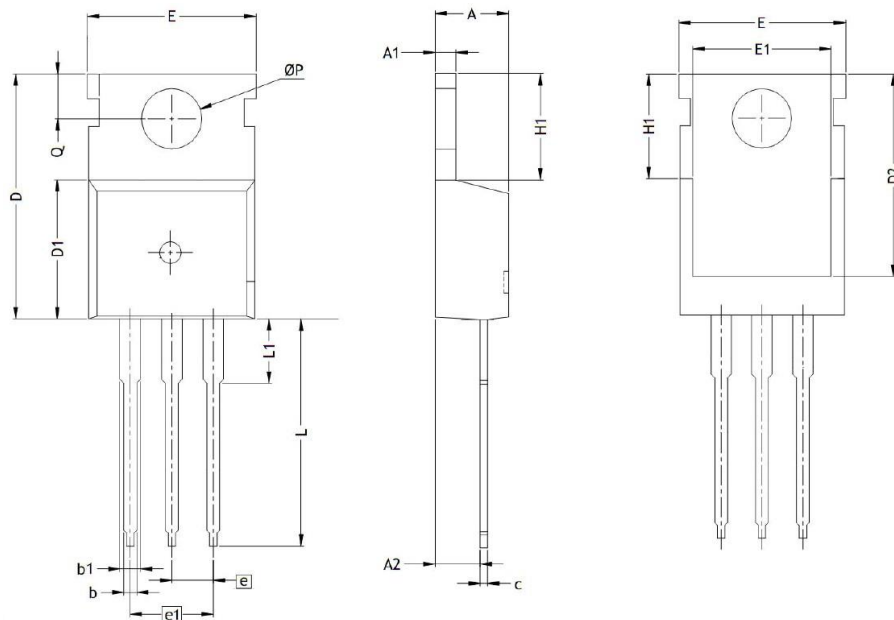
Gate Charge



Q_G - Gate Charge (nC)

8. Package Dimensions

TO-220 Package



Symbol	Dimensions In Millimeters	
	MIN.	MAX.
A	4.25	4.65
A1	1.25	1.35
A2	2.35	2.55
b	0.70	0.90
b1	1.15	1.75
c	0.45	0.61
D	14.35	16.51
D1	8.58	9.50
D2	13.05	13.65
E	9.90	10.50
E1	7.85	8.89
e	2.54BSC	
e1	5.08BSC	
H1	6.30	6.65
L	12.85	13.50
L1	2.85	3.25
ØP	3.53	4.09
Q	2.70	2.93